

**IN THE SPECIFICATION:**

The specification as amended below with replacement paragraphs shows added text with underlining and deleted text with ~~striketrough~~.

**Please REPLACE the paragraph [0006] and [0009] with the following paragraphs:**

**[0006]** The power semiconductor component may be formed of silicon. There is a clear distinction between a thermal expansion coefficient of copper and the thermal expansion coefficient of silicon. This means that very high mechanical stresses within the system comprising a power semiconductor component and a connecting lead can occur during operation of the power semiconductor component; ~~there can be~~. These high mechanical stresses can lead to interruption of the electrical contact between the connecting lead and the contact surface of the power semiconductor component.

**[0009]** The inventor proposes ~~One possible object is achieved by specifying a system~~ comprising at least one electrical component that is provided with at least one electrical contact surface, at least one electrical connecting lead for electrically contacting the contact surface of the component and at least one electrical insulating layer, which is disposed on the component and encompasses at least one opening. Said opening is continuous in the direction of the thickness of the insulating layer and is arranged so as to lie opposite the contact surface of the component. The insulating layer is provided with a lateral surface that delimits the opening while the electrical connecting lead is provided with at least one metallization layer located on the lateral surface. The system is characterized in that the metallization layer is oriented at an angle to the contact surface. The metallization layer is applied to both the contact surface of the component and the lateral surface of the insulating layer.